



MMG200S060B6N

600V 200A IGBT Module

RoHS Compliant

JULY 2010

PRELIMINARY

FEATURES

- Ultra Low Loss
- High Ruggedness
- High Short Circuit Capability
- Positive Temperature Coefficient
- Integrated Gate Resistor

APPLICATIONS

- Invector
- Converter
- Welder
- SMPS and UPS
- Induction Heating



ABSOLUTE MAXIMUM RATINGS

$T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Values	Unit
IGBT				
V_{CES}	Collector - Emitter Voltage		600	V
V_{GES}	Gate - Emitter Voltage		± 20	V
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}$	230	A
		$T_C=50^{\circ}\text{C}$	200	A
I_{Cpuls}	Pulsed Collector Current	$T_C=25^{\circ}\text{C}, t_p=1\text{ms}$	460	A
		$T_C=50^{\circ}\text{C}, t_p=1\text{ms}$	400	A
P_{tot}	Power Dissipation Per IGBT		735	W
T_J	Junction Temperature Range		-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range		-40 to +125	$^{\circ}\text{C}$
V_{isol}	Insulation Test Voltage	AC, $t=1\text{min}$	3000	V
Free-Wheeling Diode				
V_{RRM}	Repetitive Reverse Voltage		600	V
$I_{F(AV)}$	Average Forward Current	$T_C=25^{\circ}\text{C}$	200	A
		$T_C=50^{\circ}\text{C}$	160	A
$I_{F(RMS)}$	RMS Forward Current		285	A
I_{FSM}	Non-Repetitive Surge Forward Current	$T_J=45^{\circ}\text{C}, t=10\text{ms}, \text{Sine}$	600	A
		$T_J=45^{\circ}\text{C}, t=8.3\text{ms}, \text{Sine}$	660	A

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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
IGBT						
$V_{GE(th)}$	Gate - Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=4\text{mA}$	4.5	5.5	6.5	V
$V_{CE(sat)}$	Collector - Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		1.95	2.45	V
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.2		V
I_{CES}	Collector Leakage Current	$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			0.5	mA
		$V_{CE}=600\text{V}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1		mA
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}$	-0.6		0.6	μA
R_{Gint}	Integrated Gate Resistor			5	7	Ω
Q_{ge}	Gate Charge	$V_{CC}=300\text{V}, I_C=200\text{A}, V_{GE}=\pm 15\text{V}$		890		nC
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		9		nF
C_{oes}	Output Capacitance			0.9		nF
C_{res}	Reverse Transfer Capacitance			0.8		nF
$t_{d(on)}$	Turn - on Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}$ $R_G = 1.5 \Omega, V_{GE}=\pm 15\text{V}$ $T_J=25^\circ\text{C}$ Inductive Load		163		ns
t_r	Rise Time			43		ns
$t_{d(off)}$	Turn - off Delay Time			253		ns
t_f	Fall Time			33		ns
$t_{d(on)}$	Turn - on Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}$ $R_G = 1.5 \Omega, V_{GE}=\pm 15\text{V}$ $T_J=125^\circ\text{C}$ Inductive Load		180		ns
t_r	Rise Time			49		ns
$t_{d(off)}$	Turn - off Delay Time			285		ns
t_f	Fall Time			41		ns
E_{on}	Turn - on Switching Energy	$V_{CC}=300\text{V}, I_C=200\text{A}$ $R_G = 1.5 \Omega$	$T_J=25^\circ\text{C}$		3	mJ
			$T_J=125^\circ\text{C}$		4.6	mJ
E_{off}	Turn - off Switching Energy	$V_{GE}=\pm 15\text{V}$ Inductive Load	$T_J=25^\circ\text{C}$		4.1	mJ
			$T_J=125^\circ\text{C}$		6.3	mJ
Free-Wheeling Diode						
V_F	Forward Voltage	$I_F=200\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.25	1.6	V
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.2		V
t_{rr}	Reverse Recovery Time	$I_F=200\text{A}, V_R=300\text{V}$		249		ns
I_{RRM}	Max. Reverse Recovery Current	$di_F/dt=-1000\text{A}/\mu\text{s}$		107		A
Q_{rr}	Reverse Recovery Charge	$T_J=125^\circ\text{C}$		15.5		μC

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
R_{thJC}	Junction-to-Case Thermal Resistance	Per IGBT			0.17	K/W
R_{thJD}	Junction-to-Case Thermal Resistance	Per Inverse Diode			0.3	K/W
Torque	Module-to-Sink	Recommended (M6)	3		5	N · m
Torque	Module Electrodes	Recommended (M5)	2.5		5	N · m
Weight				150		g

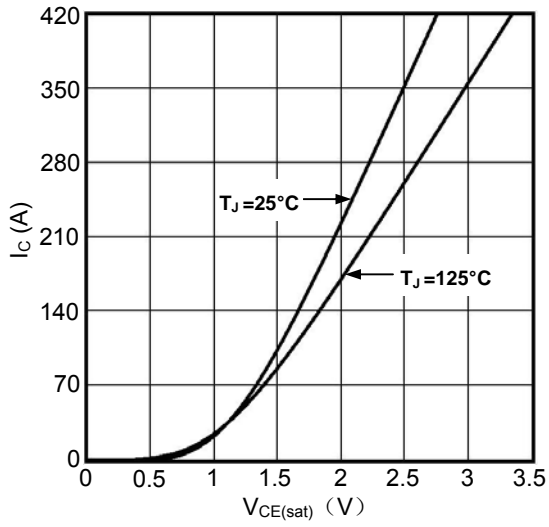


Figure1. Typical Output characteristics

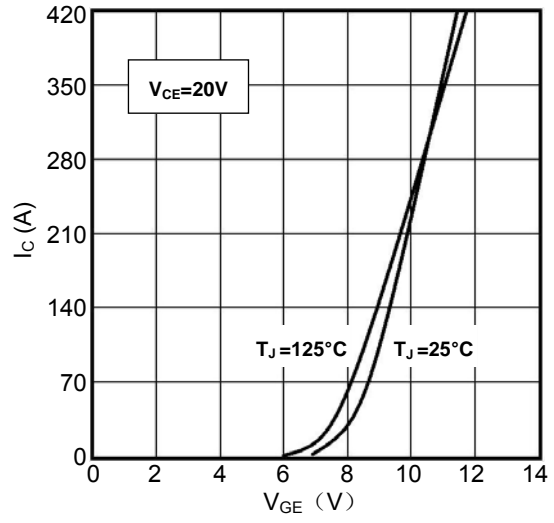


Figure2. Typical Transfer characteristics

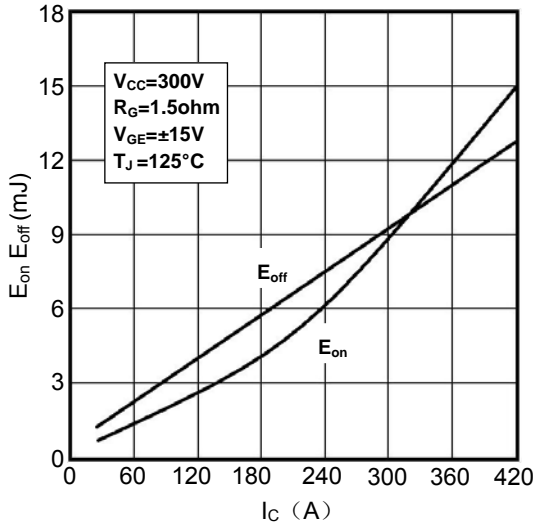


Figure3. Switching Energy vs. Collector Current

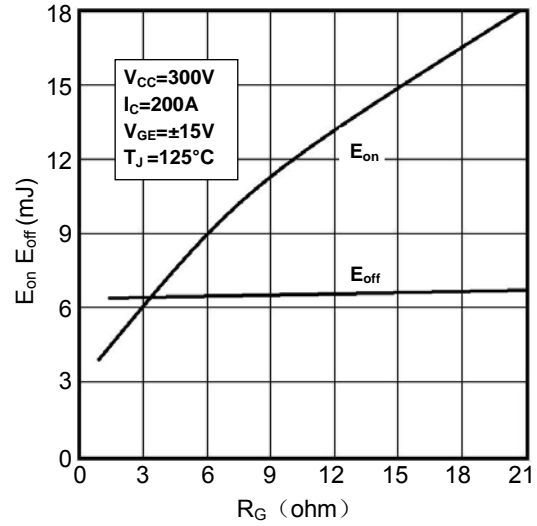


Figure4. Switching Energy vs. Gate Resistor

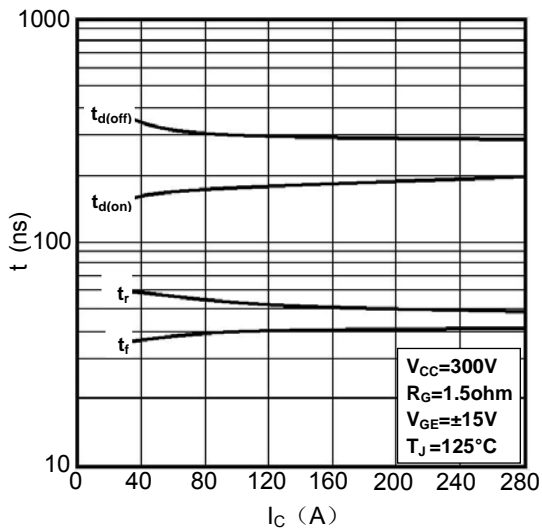


Figure5. Switching Times vs. Collector Current

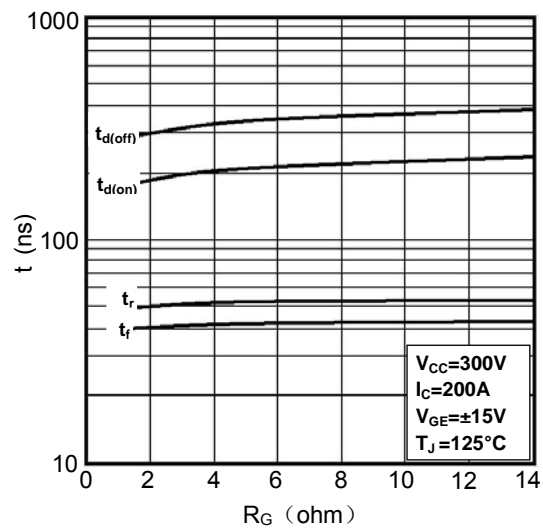


Figure6. Switching Times vs. Gate Resistor

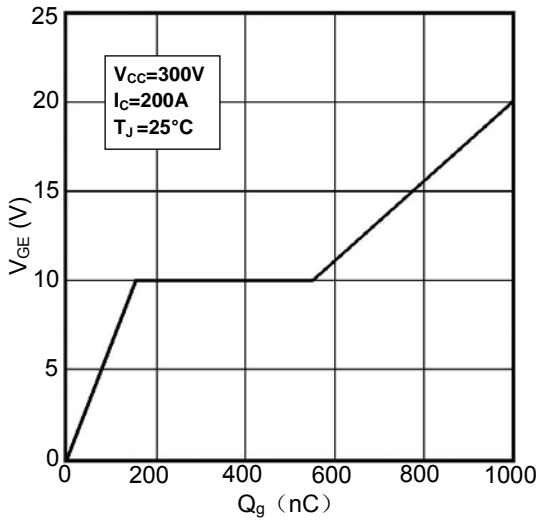


Figure7. Gate Charge characteristics

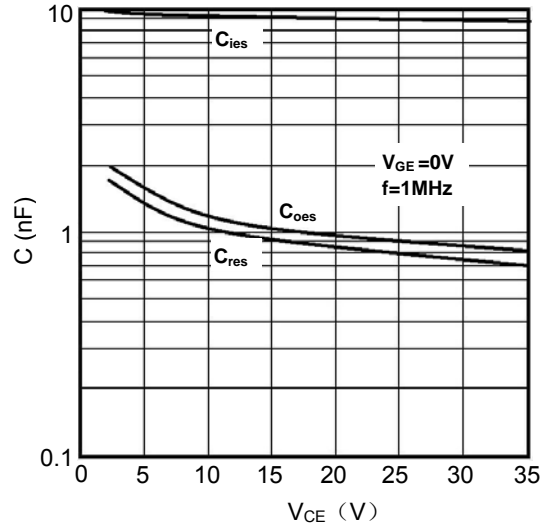


Figure8. Typical Capacitances vs. V_{CE}

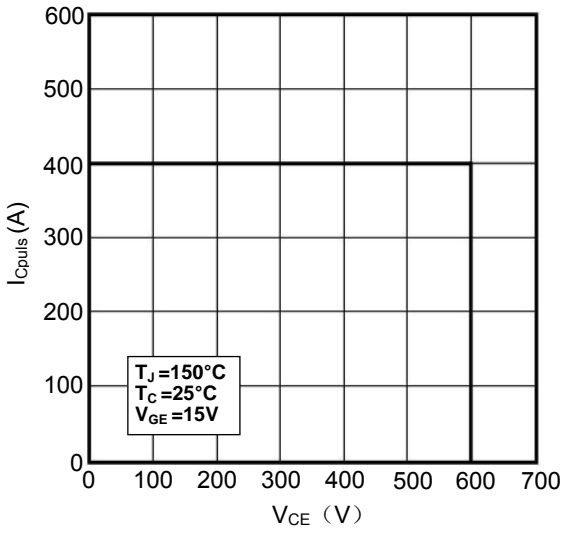


Figure9. Reverse Biased Safe Operating Area

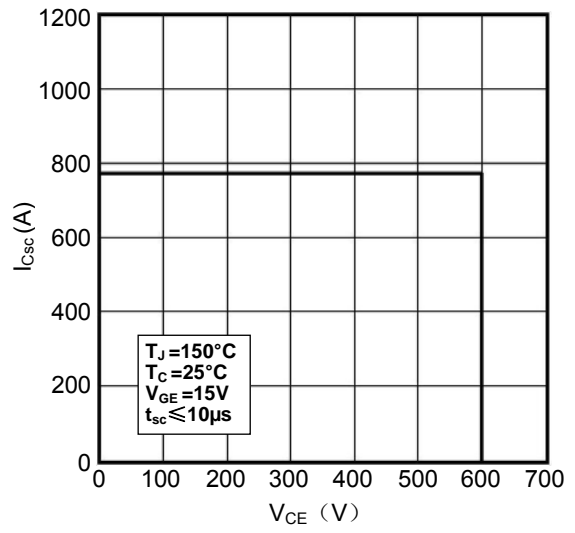


Figure10. Short Circuit Safe Operating Area

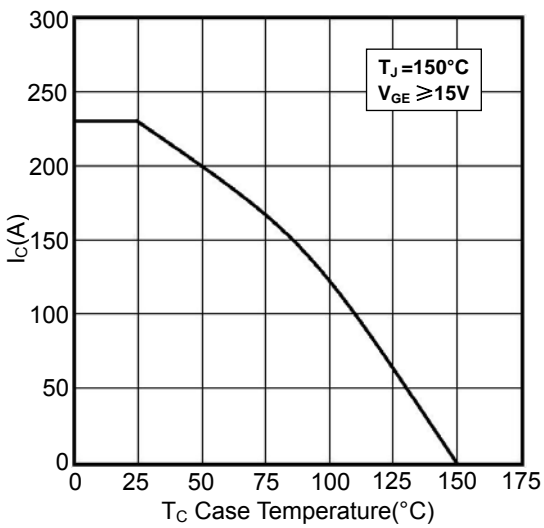


Figure11. Rated Current vs. T_C

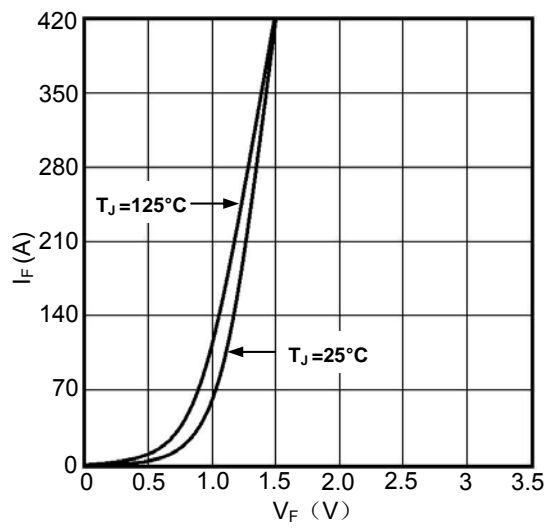
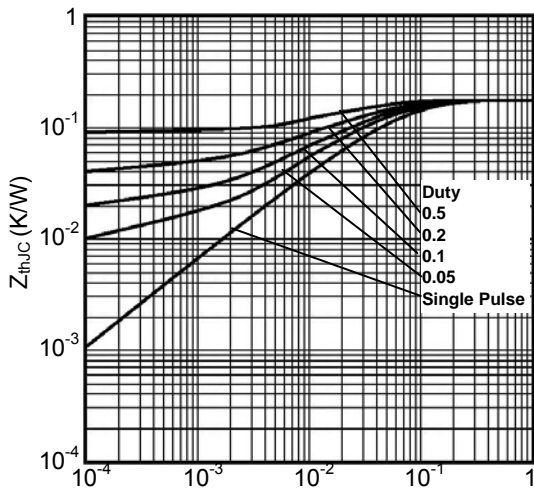
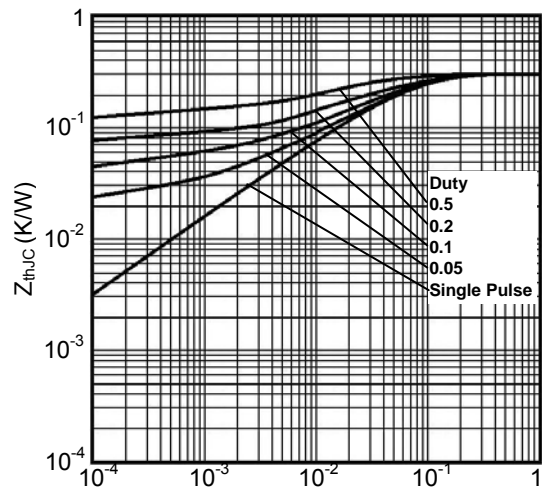


Figure12. Diode Forward Characteristics



Rectangular Pulse Duration (seconds)
Figure13. Transient Thermal Impedance of IGBT



Rectangular Pulse Duration (seconds)
Figure14. Transient Thermal Impedance of Diode

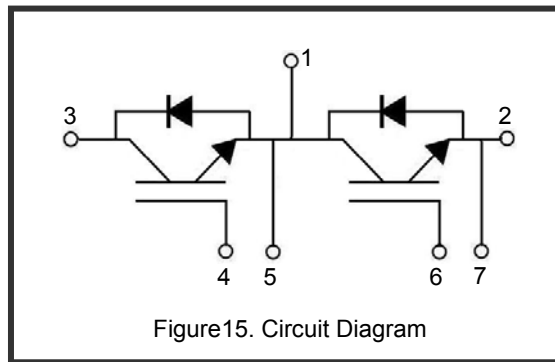


Figure15. Circuit Diagram

